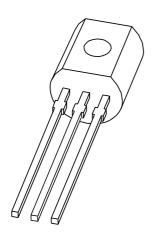
### **DISCRETE SEMICONDUCTORS**

# DATA SHEET



BC549; BC550 NPN general purpose transistors

Product specification Supersedes data of 1997 Jun 20 1999 Apr 22





### **NPN** general purpose transistors

BC549; BC550

### **FEATURES**

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

### **APPLICATIONS**

• Low noise stages in audio frequency equipment.

### **DESCRIPTION**

NPN transistor in a TO-92; SOT54 plastic package. PNP complements: BC559 and BC560.

### **PINNING**

PIN	DESCRIPTION
1	emitter
2	base
3	collector

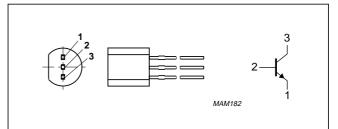


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter			
	BC549		_	30	V
	BC550		_	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base			
	BC549		_	30	V
	BC550		_	45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
Ic	collector current (DC)		_	100	mA
I <sub>CM</sub>	peak collector current		_	200	mA
I <sub>BM</sub>	peak base current		_	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	_	500	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature			150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

### Note

1. Transistor mounted on an FR4 printed-circuit board.

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### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	250	K/W

### Note

1. Transistor mounted on an FR4 printed-circuit board.

### **CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified.

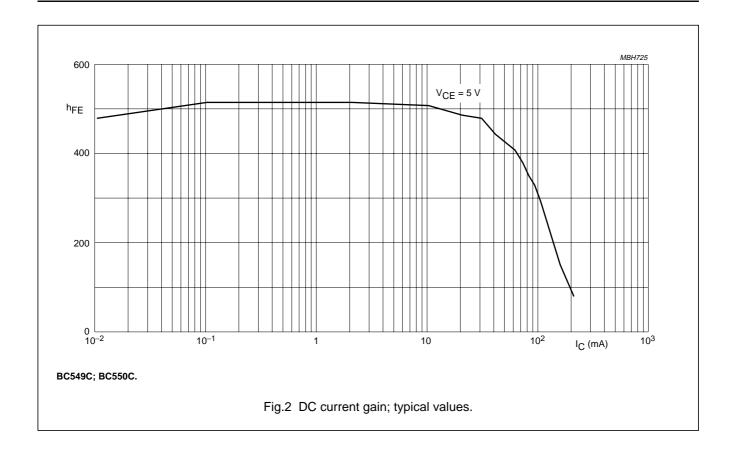
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 30 V	_	_	15	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = 30 V; T <sub>j</sub> = 150 °C	_	_	5	μΑ
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 5 V	_	_	100	nA
h <sub>FE</sub>	DC current gain					
	BC549C; BC550C	$I_C = 10 \mu A; V_{CE} = 5 V; see Fig.2$	-	270	-	
		I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V; see Fig.2	420	520	800	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	90	250	mV
		I <sub>C</sub> = 100 mA; I <sub>B</sub> = 5 mA	_	200	600	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C = 10 \text{ mA}$ ; $I_B = 0.5 \text{ mA}$ ; note 1	_	700	_	mV
		$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}; \text{ note 1}$	_	900	_	mV
V <sub>BE</sub>	base-emitter voltage	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V; note 2	580	660	700	mV
		I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V; note 2	_	_	770	mV
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz	_	1.5	_	pF
C <sub>e</sub>	emitter capacitance	$I_C = I_c = 0$ ; $V_{EB} = 0.5 \text{ V}$ ; $f = 1 \text{ MHz}$	_	11	_	pF
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 5 V; f = 100 MHz	100	-	_	MHz
F	noise figure	$I_C$ = 200 μA; $V_{CE}$ = 5 V; $R_S$ = 2 kΩ; f = 10 Hz to 15.7 kHz	_	_	4	dB
		$I_C$ = 200 μA; $V_{CE}$ = 5 V; $R_S$ = 2 kΩ; f = 1 kHz; B = 200 Hz	_	_	4	dB

### **Notes**

- 1. V<sub>BEsat</sub> decreases by about 1.7 mV/K with increasing temperature.
- 2.  $V_{BE}$  decreases by about 2 mV/K with increasing temperature.

## NPN general purpose transistors

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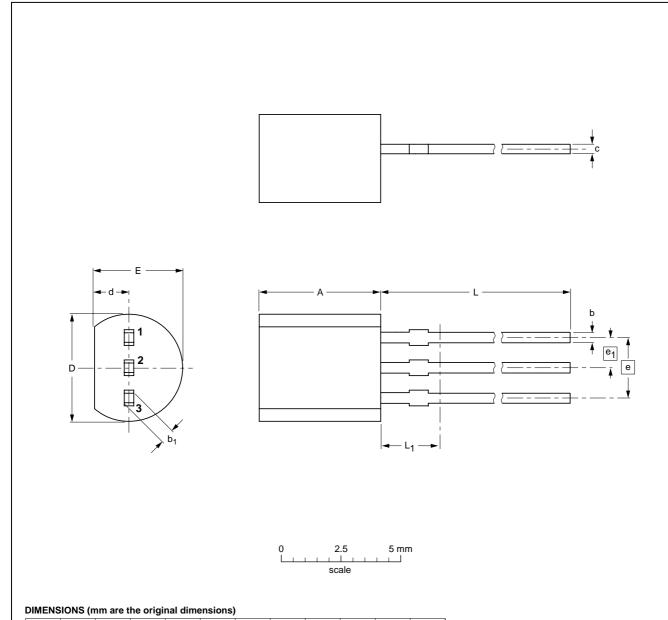
### NPN general purpose transistors

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### **PACKAGE OUTLINE**

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



UNIT	A	b	b <sub>1</sub>	С	D	d	E	е	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup>
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

#### Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

	OUTLINE		REFERENCES			EUROPEAN ISSUE DATE		IGGIIE DAT		
VERSION		IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE			
	SOT54		TO-92	SC-43			97-02-28			

### NPN general purpose transistors

BC549; BC550

### **DEFINITIONS**

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

### Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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BC549; BC550

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